

**Amendments to the Claims:**

Cancel claims 16-32 without prejudice.

**Listing of claims:**

Claims 1-15 (original).

Claims 16-32 (cancelled).

**Text of pending claims**

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1. (Original) A cleaning polish etch composition for treating a superfinished surface of a substrate, the cleaning polish etch composition consisting essentially of:

a carrying fluid;

etchant for etching the substrate and/or attached slurry particles.

2. (Original) The cleaning polish etch composition as recited in claim 1, wherein the substrate is selected from a group consisting of a glass disk substrate, a ceramic disk substrate, and a glass-ceramic disk substrate for use in a data storage device.

3. (Original) The cleaning polish etch composition as recited in claim 2, wherein the substrate is a silicate-based glass disk substrate.

4. (Original) The cleaning polish etch composition as recited in claim 3, wherein the cleaning polish etch composition has a pH of approximately 0 to 4.

5. (Original) The cleaning polish etch composition as recited in claim 4, wherein the cleaning polish etch composition has a pH of approximately 0.8 to 3.0.

6. (Original) The cleaning polish etch composition as recited in claim 5, wherein the cleaning polish etch composition has a pH of approximately 1.0 to 2.0.

7. (Original) The cleaning polish etch composition as recited in claim 1, wherein the substrate is a head wafer selected from a group consisting of Sendust and Permalloy.

8. (Original) The cleaning polish etch composition as recited in claim 7, wherein the substrate is a Sendust head wafer.

9. (Original) The cleaning polish etch composition as recited in claim 8, wherein the cleaning polish etch composition has a pH of approximately 6 to 10.

10. (Original) The cleaning polish etch composition as recited in claim 9, wherein the cleaning polish etch composition has a pH of approximately 9.5 to 10.

11. (Original) The cleaning polish etch composition as recited in claim 1, wherein the etchant is an acid or base solution.

12. (Original) The cleaning polish etch composition as recited in claim 3, wherein the etchant is a metal etchant selected from a group of consisting of Ce, Zr, Ti, Fe, Sn, Al, Cr, Ni, Mn and Zn, and combinations thereof.

13. (Original) The cleaning polish etch composition as recited in claim 12, wherein the metal etchant is Ce.

14. (Original) The cleaning polish etch composition as recited in claim 8, wherein the etchant is a metal etchant selected from a group consisting of Ce, Zr, Ti, Fe, Sn, Al, Cr, Ni, Mn and Zn, and combinations thereof.

15. (Original) The cleaning polish etch composition as recited in claim 14, wherein the metal etchant is Fe.

**Election to Restriction**

Applicants elect Group I, claims 1-15 for further prosecution, and cancel claims 16-32 without prejudice.